

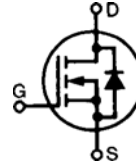
HiPerFET™ Power MOSFETs Q-Class

N-Channel Enhancement Mode
Avalanche Rated,
Low Q_g , High dv/dt
Preliminary Data

IXFH20N80Q
IXFK20N80Q
IXFT20N80Q

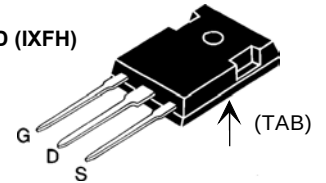
$V_{DSS} = 800 \text{ V}$
 $I_{D25} = 20 \text{ A}$
 $R_{DS(on)} = 0.42 \Omega$

$t_{rr} \leq 250 \text{ ns}$

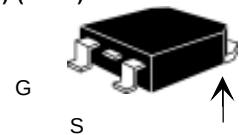


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	800	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	20	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	80	A
I_{AR}	$T_C = 25^\circ\text{C}$	20	A
E_{AR}	$T_C = 25^\circ\text{C}$	45	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2 \Omega$	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	360	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.063 in) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	TO-247 TO-264	1.13/10 Nm/lb.in. 0.9/6 Nm/lb.in.
Weight		TO-247 TO-268 TO-264	6 4 10 g

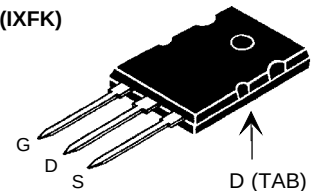
TO-247 AD (IXFH)



TO-268 (D3) (IXFT)



TO-264 AA (IXFK)



G = Gate
S = Source

TAB = Drain

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4 \text{ mA}$	2.5		4.5 V
I_{GSS}	$V_{GS} = \pm 20 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0 \text{ V}$			25 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			0.42 Ω

Features

- IXYS advanced low Q_g process
- International standard packages
- Epoxy meet UL 94 V-0, flammability classification
- Low $R_{DS(on)}$ low Q_g
- Avalanche energy and current rated
- Fast intrinsic rectifier

Advantages

- Easy to mount
- Space savings
- High power density

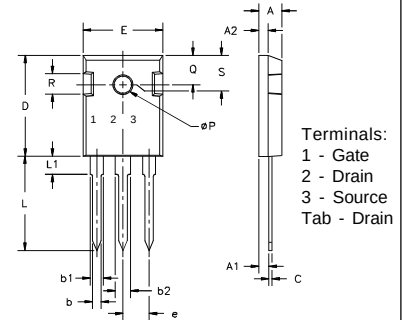
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$V_{DS} = 10\text{ V}; I_D = 0.5 \cdot I_{D25}$, pulse test	11	19	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		5100	pF
C_{oss}			500	pF
C_{rss}			170	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 1.5\ \Omega$ (External),		28	ns
t_r			27	ns
$t_{d(off)}$			74	ns
t_f			14	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		150	nC
Q_{gs}			34	nC
Q_{gd}			80	nC
R_{thJC}			0.35	K/W
R_{thCK}	TO-247		0.25	K/W
	TO-264		0.15	K/W

Source-Drain Diode

Characteristic Values
($T_J = 25^\circ\text{C}$, unless otherwise specified)

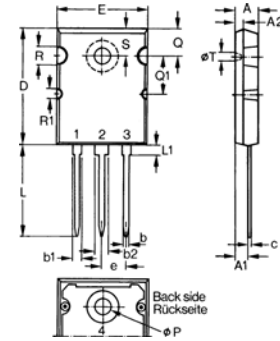
Symbol	Test Conditions	min.	typ.	max.
I_S	$V_{GS} = 0\text{ V}$			20 A
I_{SM}	Repetitive; pulse width limited by T_{JM}			80 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = I_S - di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		1	250 ns
Q_{RM}			9	μC
I_{RM}				A

TO-247 AD (IXFH) Outline



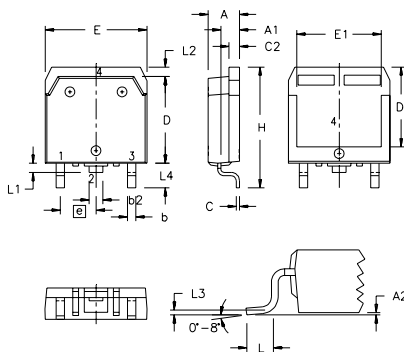
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-264 AA Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.82	5.13	.190	.202
A ₁	2.54	2.89	.100	.114
A ₂	2.00	2.10	.079	.083
b	1.12	1.42	.044	.056
b ₁	2.39	2.69	.094	.106
b ₂	2.90	3.09	.114	.122
c	0.53	0.83	.021	.033
D	25.91	26.16	1.020	1.030
E	19.81	19.96	.780	.786
e	5.46 BSC		.215 BSC	
J	0.00	0.25	.000	.010
K	0.00	0.25	.000	.010
L	20.32	20.83	.800	.820
L1	2.29	2.59	.090	.102
P	3.17	3.66	.125	.144
Q	6.07	6.27	.239	.247
Q1	8.38	8.69	.330	.342
R	3.81	4.32	.150	.170
R1	1.78	2.29	.070	.090
S	6.04	6.30	.238	.248
T	1.57	1.83	.062	.072

TO-268 Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A ₁	.106	.114	2.70	2.90
A ₂	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b ₂	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C2	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D1	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E1	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L1	.047	.055	1.20	1.40
L2	.039	.045	1.00	1.15
L3	.010 BSC		0.25 BSC	
L4	.150	.161	3.80	4.10

IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	